

# Wide Bandgap Device for Microwave and Power Electronics Applications

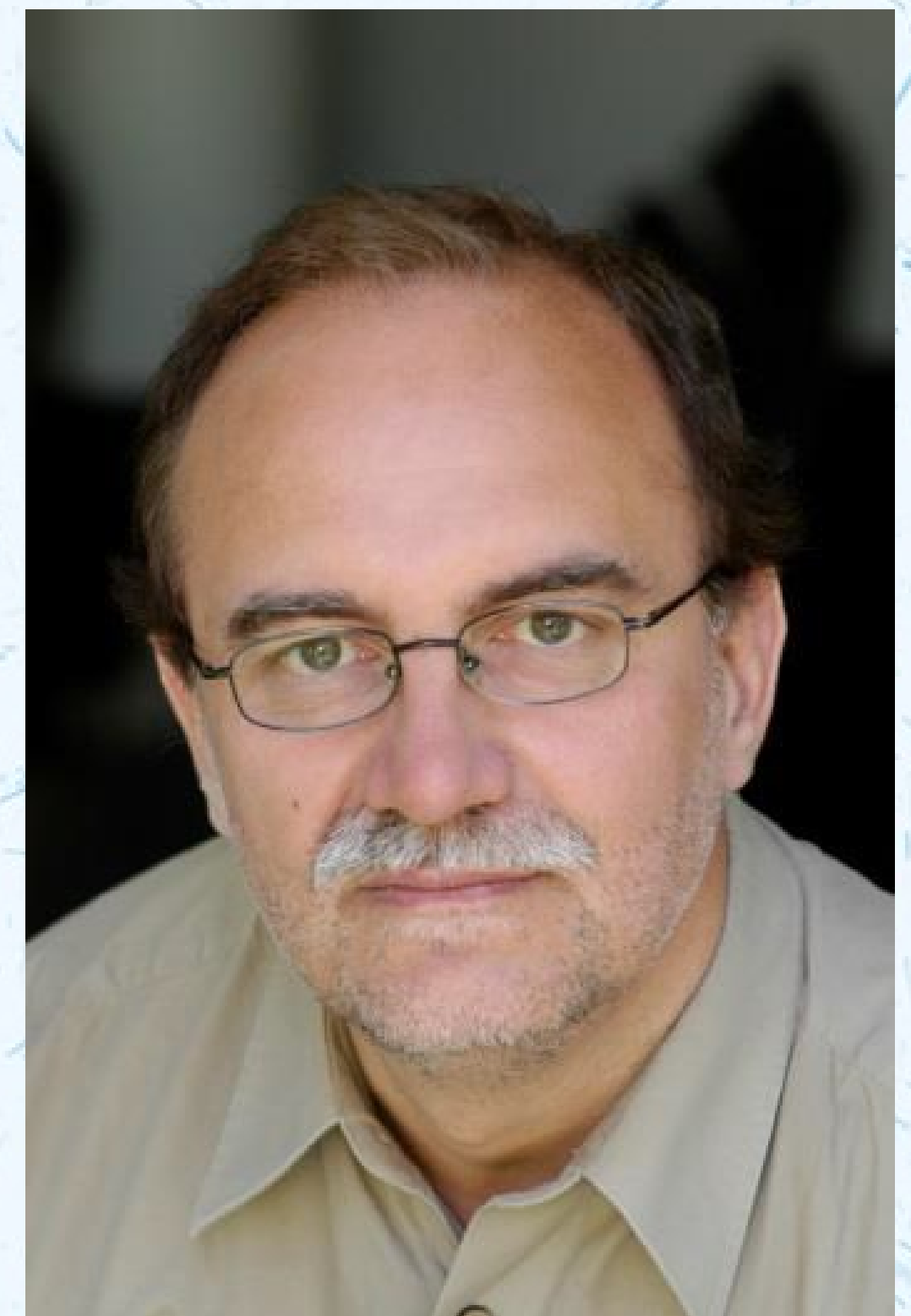
**Lecturer** Dr.-Ing. Joachim Würfl

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Joachim Würfl received the Ph.D. degree in electrical engineering from the Technical University of Darmstadt, Darmstadt, Germany, in 1989.

He is managing projects on GaN-based L- and X-band power devices and MMICs, high-voltage power devices, and high-frequency low-noise amplifiers.

He is responsible for the design, technological implementation, characterization, and reliability testing of these devices.



**Venue** MIRC 201

Date and Time	Title
10/29 13:20~16:20	Introduction and Basic Understanding
10/31 18:20~21:20	Technological Implementation
11/1 18:20~21:20	Electrical properties and reliability
11/5 13:20~16:20	GaN Microwave and THz Devices
11/7 18:20~21:20	GaN Power Switching Devices
11/8 18:20~21:20	Explorative Wide Bandgap Devices, future topics